

D. Thin Film Process Technology **분과**

Room F
창의관 (B114)

일 시 : 2월 16일(목) 11:20-12:35

세션명 : [TF2-D] Resistive Memory

좌 장 : 황기현(삼성전자), 박태주(한양대학교)

TF2-D-1 11:20-11:50 **[Invited] Emerging Memories: Resistive Switching Mechanisms and Current Status**

저자: Doo Seok Jeong

소속: Electronic Materials Research Centre, Korea Institute of Science and Technology

TF2-D-2 11:50-12:05 **Memristive Tri-stable Resistive Switching at Ruptured Conducting Filaments of a Pt/TiO₂/Pt Cell**

저자: Kyung Jean Yoon, Min Hwan Lee, Gun Hwan Kim, Seul Ji Song, Jun Yeong Seok, Jung Ho Yoon, and Cheol Seong Hwang

소속: WCU Hybrid Materials Program, Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University

TF2-D-3 12:05-12:20 **Plasma-enhanced Atomic Layer Deposition of NiO Thin Films for Resistive Switching Memory Applications**

저자: Seul Ji Song¹, Gun Hwan Kim¹, Jun Yeong Seok¹, Kyung Jean Yoon¹, Julien Gatineau², and Cheol Seong Hwang¹

소속: ¹WCU Hybrid Materials Program, Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University, ²Air Liquide

TF2-D-4 12:20-12:35 **Effect of TaOx Composition and HfO₂ Physical Property on Bipolar Resistive Switching Behavior of Pt/HfO₂/TaOx/Pt Device**

저자: 김종기¹, 이성훈^{1,2}, 김영재¹, 나희도¹, 이규민¹, 박성훈¹, 손현철¹

소속: ¹연세대학교 신소재공학과, ²㈜하이닉스반도체